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MCP2003B

LIN Transceiver

Features

- The MCP2003B is Compliant with Local Interconnect Network (LIN) Bus Specifications 1.3, 2.0, 2.1, 2.2, SAE J2602, and ISO17987
- Supports Baud Rates up to 20 Kbaud with LIN-Compatible Output Driver
- 60V Load Dump Protected
- Very High Electromagnetic Immunity (EMI) Meets Stringent Original Equipment Manufacturers (OEM) Requirements
- Direct Capacitor Coupling Robustness without Transient Voltage Suppressor (TVS):
  - ±35V on LBUS (SAE J2962-1)
  - ±85V on LBUS (SAE J2962-1)
- High Electrostatic Discharge (ESD) Immunity without TVS:
  - >25 kV on LBUS (SAE J2962-1)
  - >15 kV on VBB (IEC 61000-4-2)
  - >6 kV on LBUS (IEC 61000-4-2)
- Very High Immunity to RF Disturbances Meets Stringent OEM Requirements
- Wide Supply Voltage: 5.5V – 30.0V Continuous
- Extended (E) Temperature Range: -40°C to +125°C
- High (H) Temperature Range: -40°C to +150°C
- Interfaces to PIC® MCU EUSART and Standard USARTs
- LIN Bus Pin:
  - Internal pull-up resistor and diode
  - Protected against battery shorts
  - Protected against loss of ground
  - High current drive: >40 mA
- Automatic Thermal Shutdown
- Low-Power Mode:
  - Receiver monitoring bus and transmitter off: (≅ 5 µA)

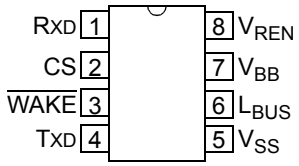
LOCAL INTERCONNECT NETWORK

Description

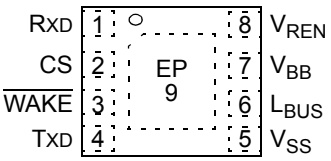
This device provides a bidirectional, half-duplex communication, physical interface to automotive and industrial LIN systems to meet the LIN Bus Specification Revision 2.2, SAE J2602, and ISO 17987. The device is both short-circuit and overtemperature protected by internal circuitry. The device has been specifically designed to operate in the automotive operating environment and will survive all specified transient conditions while meeting all of the stringent quiescent current requirements.

Package Types

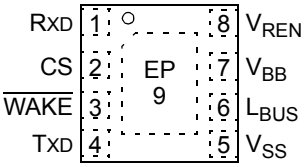
MCP2003B
SOIC



MCP2003B
2x3 DFN*



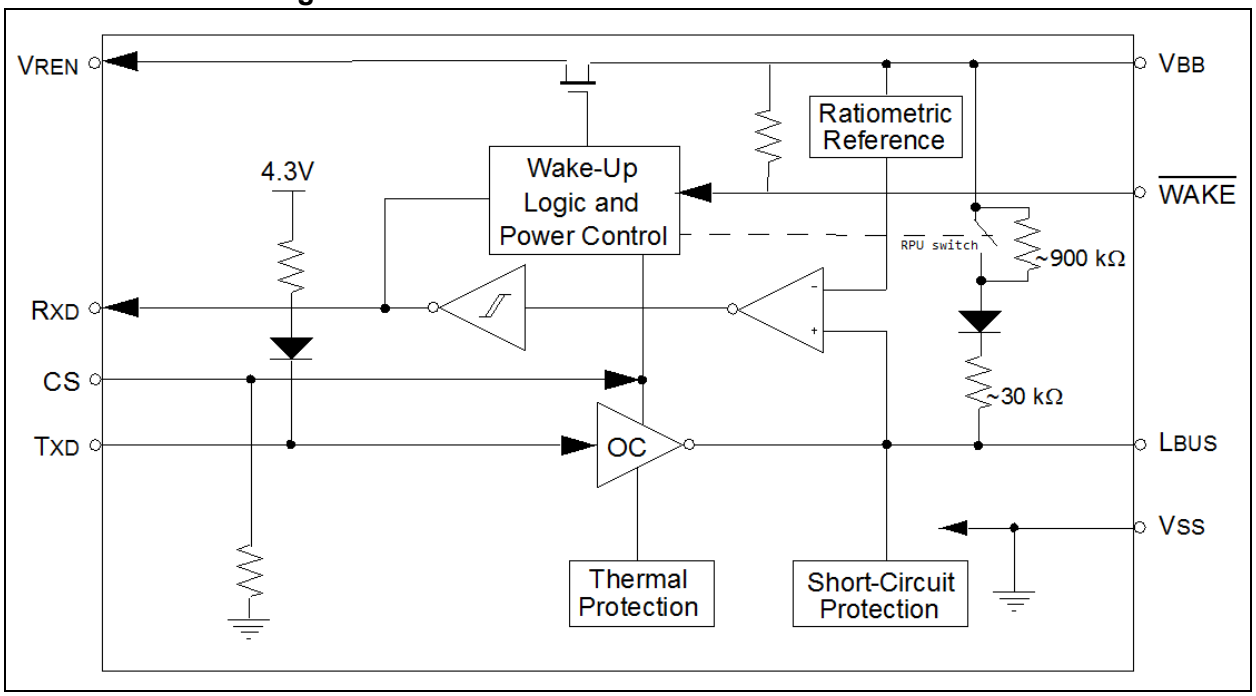
MCP2003B
3x3 DFN*



* Includes Exposed Thermal Pad (EP); see Table 1-2.

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MCP2003B Block Diagram



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1.0 DEVICE OVERVIEW

The MCP2003B devices provide a physical interface between a microcontroller and a LIN bus. These devices will translate the CMOS/TTL logic levels to LIN logic level, and vice versa. It is intended for automotive and industrial applications with serial bus speeds up to 20 Kbaud.

LIN Bus Specification Revision 2.2 requires that the transceiver of all nodes in the system is connected via the LIN pin, referenced to ground and with a maximum external termination resistance load of 510Ω from LIN bus to battery supply. The 510Ω corresponds to 1 master and 15 slave nodes.

The VREN pin can be used to drive the logic input of an external voltage regulator. This pin is high in all modes except for Power-Down mode.

1.1 External Protection

1.1.1 REVERSE BATTERY PROTECTION

An external reverse-battery-blocking diode should be used to provide polarity protection (see Example 1-1).

1.1.2 TRANSIENT VOLTAGE PROTECTION (LOAD DUMP)

An external 60V transient suppressor (TVS) diode, between VBB and ground, with a 50Ω transient protection resistor (RTP) in series with the battery supply and the VBB pin serve to protect the device from power transients (see Example 1-1) and ESD events. While this protection is optional, it is considered good engineering practice.

1.2 Internal Protection

1.2.1 ESD PROTECTION

For component-level ESD ratings, please refer to the maximum operation specifications.

1.2.2 GROUND LOSS PROTECTION

The LIN Bus specification states that the LIN pin must transition to the recessive state when ground is disconnected. Therefore, a loss of ground effectively forces the LIN line to a high-impedance level.

1.2.3 THERMAL PROTECTION

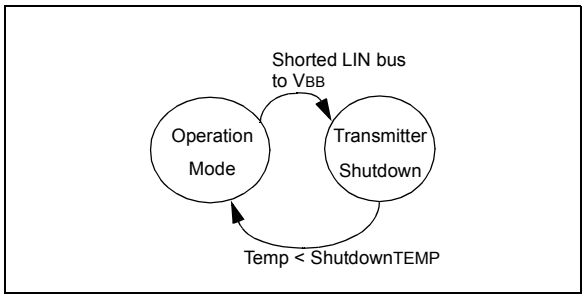
The thermal protection circuit monitors the die temperature and is able to shut down the LIN transmitter.

There are two causes for a thermal overload. A thermal shutdown can be triggered by either, or both, of the following thermal overload conditions.

- LIN bus output overload
- Increase in die temperature due to increase in environment temperature

Driving the TXD and checking the RXD pin makes it possible to determine whether there is a bus contention (RX = low, TX = high) or a thermal overload condition (RX = high, TX = low). After a thermal overload event, the device will automatically recover once the die temperature has fallen below the recovery temperature threshold (see Figure 1-1).

FIGURE 1-1: THERMAL SHUTDOWN STATE DIAGRAM



1.3 Modes of Operation

For an overview of all operational modes, refer to Table 1-1.

1.3.1 POWER-DOWN MODE

In Power-Down mode, everything is off except the wake-up section. The internal 30 kΩ pull-up resistor switch is open, which enables the high ohmic pull-up resistor (900 kΩ typical). This is the lowest power mode. The receiver is off, thus its output is open-drain.

On CS going to a high level or a falling edge on $\overline{\text{WAKE}}$, the device will enter Ready mode as soon as internal voltage stabilizes. Refer to **Section 2.4 "AC Specifications"** for further information. In addition, LIN bus activity will change the device from Power-Down mode to Ready mode; The MCP2003B wakes up on a rising edge on LBUS preceded by a low level lasting at least 70 µs typically. See Figure 1-2 about remote wake-up. If CS is held high as the device transitions from Power-Down to Ready mode, the device will transition to either Operation or Transmitter Off mode, depending on TXD input, as soon as internal voltages stabilize.

1.3.2 READY MODE

Transitioning from POR into Ready mode is achieved when $V_{BB} > V_{BBUV_RISE}$. Upon entering Ready mode, VREN is enabled and the receiver detect circuit is powered-up. The transmitter remains disabled and the device is ready to receive data but not to transmit.

Upon VBB supply pin power-on, the device will remain in Ready mode as long as CS is low. When CS transitions high, the device will either enter Operation mode if the TXD pin is held high, or the device will enter Transmitter Off mode if the TXD pin is held low.

1.3.3 OPERATION MODE

In this mode, all internal modules are operational. Note that the part cannot transmit if the pull-up resistance is missing on RX pin. See **Section 1.5.1.1 "RXD Monitoring"** for details.

The device will go into Power-Down mode on the falling edge of CS and the TXD pin is held high. The device will enter Transmitter Off mode in the event of a Fault condition such as thermal overload, bus contention or TXD timer expiration.

The VBB to LBUS ~30 kΩ pull-up resistor (RSLAVE) is connected only in Operation mode.

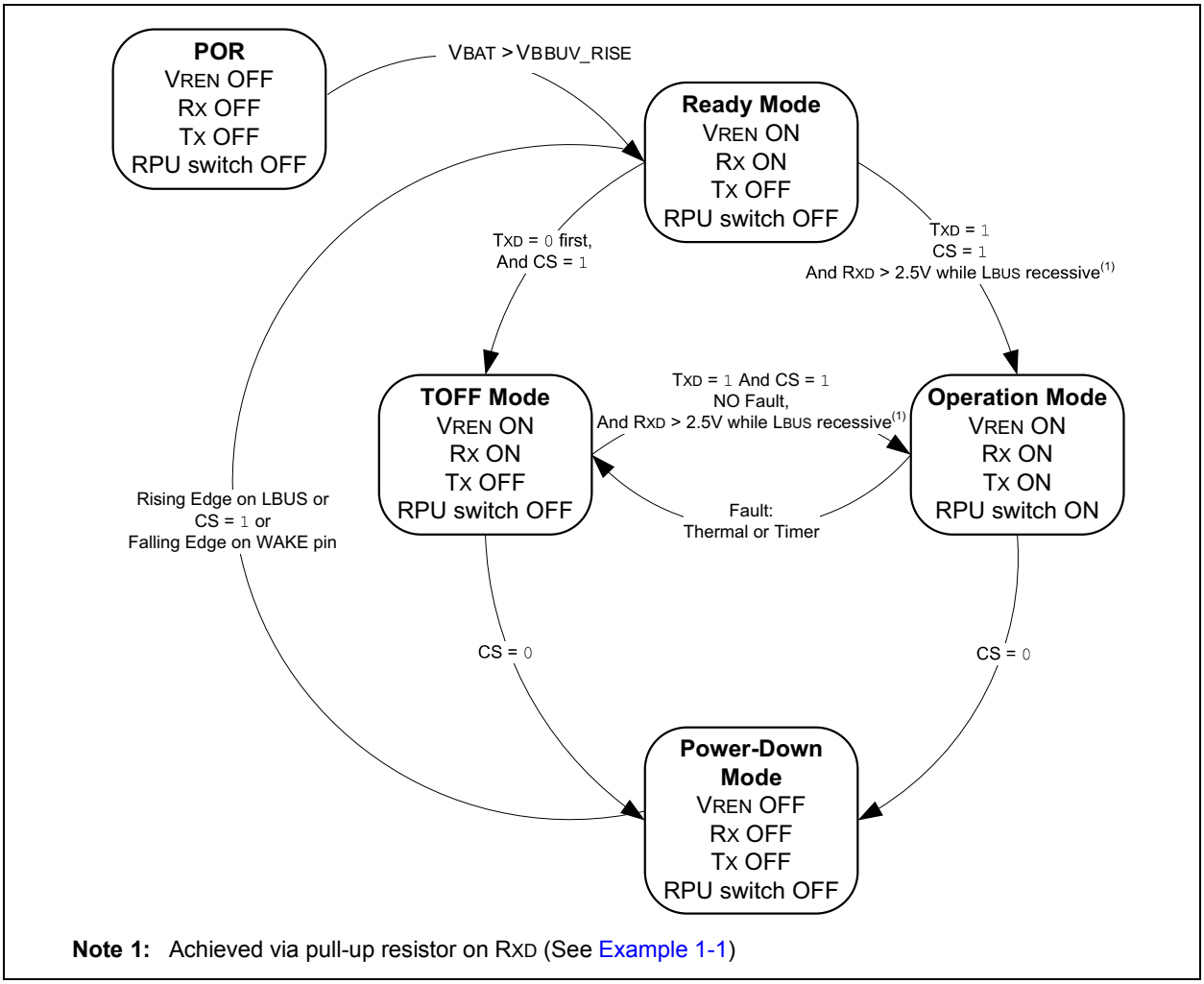
1.3.4 TRANSMITTER OFF MODE

Transmitter Off mode is reached whenever the transmitter is disabled due to a Fault condition. Fault conditions include thermal overload, bus contention, RXD monitoring and TXD timer expiration.

The device will go into Power-Down mode on the falling edge of CS, or return to Operation mode if all faults are resolved.

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FIGURE 1-2: OPERATIONAL MODES STATE DIAGRAM – MCP2003B



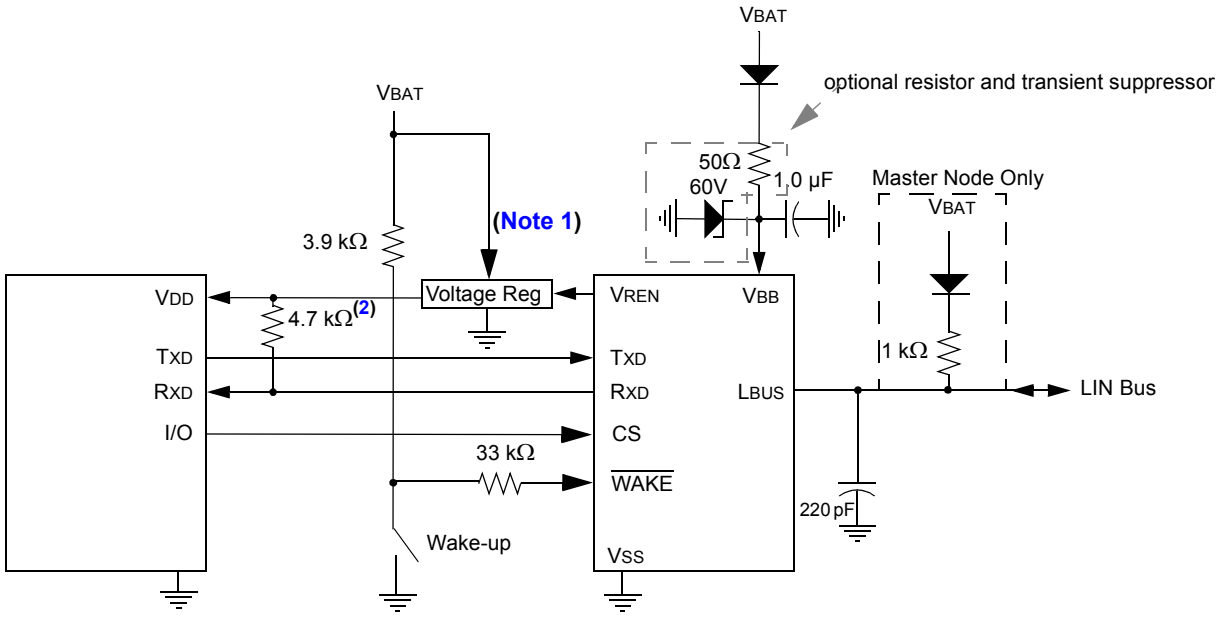
Note 1: Achieved via pull-up resistor on RXD (See Example 1-1)

TABLE 1-1: OVERVIEW OF OPERATIONAL MODES

State	Transmitter	Receiver	VREN	Operation	Comments
POR	OFF	OFF	OFF	Check CS: if low, then proceed to Ready mode; If high, transition to either TOFF or Operation mode, depending on TXD.	VBB > VBB(MIN) and Internal Supply stable. High ohmic pull-up resistor enabled (900 kΩ typical).
Ready	OFF	ON	ON	On CS high level, proceed to Operation or TOFF mode.	Bus Off state. High ohmic pull-up resistor enabled (900 kΩ typical).
Operation	ON	ON	ON	On CS low level, proceed to Power-Down. On a fault condition, proceed to TOFF mode.	Normal Operation mode. RXD has to be at a high level (>2.5V typical) while LBUS is recessive.
Power-Down	OFF	Activity Detect	OFF	On CS high level, proceed to Ready mode then proceed to either Operation or TOFF mode. Falling edge on WAKE will put the device into Ready mode. Rising edge on LIN bus will put the device into Ready mode.	Low-Power mode. High ohmic pull-up resistor enabled (900 kΩ typical).
Transmitter Off	OFF	ON	ON	On CS low level, proceed to Power-Down mode; On TXD high and no fault condition, proceed to Operation mode.	High ohmic pull-up resistor enabled (900kΩ typical).

1.4 Typical Applications

EXAMPLE 1-1: TYPICAL MCP2003B APPLICATION

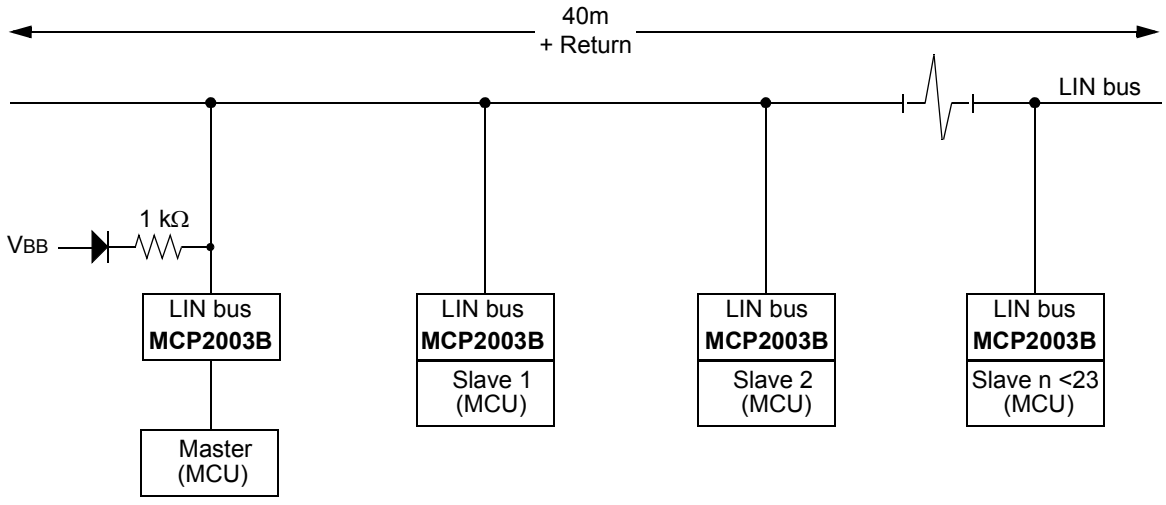


Note 1: For applications with current requirements of less than 20 mA, the connection to VBAT can be deleted, and voltage to the regulator supplied directly from the VREN pin.

2: Required for transmission.

3: A Transient Voltage Suppressor on the LIN Bus is not required to sustain SAE J2962-1 ESD and Direct Capacitor Coupling tests.

EXAMPLE 1-2: TYPICAL LIN NETWORK CONFIGURATION



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1.5 Pin Descriptions

TABLE 1-2: PINOUT DESCRIPTIONS

Pin Name	8-Lead SOIC	2x3 DFN	3x3 DFN	Normal Operation
RXD	1	1	1	Receive Data Output (OD), HV tolerant
CS	2	2	2	Chip Select (TTL), HV tolerant
$\overline{\text{WAKE}}$	3	3	3	Wake-up, HV tolerant
TXD	4	4	4	Transmit Data Input (TTL), HV tolerant
VSS	5	5	5	Ground
LBUS	6	6	6	LIN Bus (bidirectional)
VBB	7	7	7	Battery Positive
VREN	8	8	8	Voltage Regulator Enable Output
EP	—	9	9	Exposed Thermal Pad. Do not electrically connect or connect to Vss.

Legend: TTL = TTL Input Buffer; OD = Open-Drain Output

1.5.1 RECEIVE DATA OUTPUT (RXD)

The Receive Data Output pin is an open-drain (OD) output and follows the state of the LIN pin, except in Power-Down mode.

1.5.1.1 RXD Monitoring

The RXD pin is internally monitored. It has to be at a high level (> 2.5V typical) while LBUS is recessive in Operation mode. Otherwise, an internal fault will be created and the device will transition to Transmitter Off mode.

Note:	A voltage regulator sensing circuit is connected to RXD. This sensing circuit internally monitors the RXD pin when LBUS is recessive (RXD = 1). It will not allow the device to switch (or stay) in Operation Mode if the RXD pin is left open. The RXD pin must be connected to a valid supply through a pull-up resistor as RXD is an open drain pin.

1.5.2 CHIP SELECT (CS)

This is the Chip Select Input pin. An internal pull-down resistor will keep the CS pin low. This is done to ensure that no disruptive data will be present on the bus while the microcontroller is executing a Power-on Reset and an I/O initialization sequence. The pin must detect a high level to activate the transmitter. An internal Low-Pass filter, with a typical time constant of 10 µs, prevents unwanted wake-up (or transition to Power-Down mode) on glitches.

If CS = 0 when the VBB supply is turned on, the device goes to Ready mode as soon as internal voltages stabilize, and stays there as long as the CS pin is held low (0). In Ready mode, the receiver is on and the LIN transmitter driver is off.

If CS = 1 when the VBB supply is turned on, the device will proceed to Operation mode, or TXOFF (refer to Figure 1-2), as soon as internal voltages stabilize.

This pin may also be used as a local wake-up input (refer to Example 1-1). In this implementation, the microcontroller I/O controlling the CS should be converted to a high-impedance input allowing the internal pull-down resistor to keep CS low. An external switch, or other source, can then wake-up both the transceiver and the microcontroller (if powered). Refer to **Section 1.3 "Modes of Operation"**, for detailed operation of CS.

Note:	It is not recommended to tie CS high, as this can result in the device entering Operation mode before the microcontroller is initialized and may result in unintentional LIN traffic. The CS pin is internally pulled down to ground with 190 kΩ when CS is less than VIL, and 2 MΩ when CS is greater than VIH. The current on CS is limited to about 2 µA when CS is greater than VIH.

1.5.3 WAKE-UP INPUT ($\overline{\text{WAKE}}$)

The $\overline{\text{WAKE}}$ pin has an internal 800 kΩ pull-up to VBB. A falling edge on the $\overline{\text{WAKE}}$ pin causes the device to wake from Power-Down mode. Upon waking, the MCP2003B will enter Ready mode.

1.5.4 TRANSMIT DATA INPUT (TXD)

The Transmit Data Input pin has an internal pull-up. The LIN pin is low (dominant) when TXD is low, and high (recessive) when TXD is high.

For extra bus security, TXD is internally forced to '1' whenever the transmitter is disabled, regardless of external TXD voltage.

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1.5.4.1 TXD Dominant Timeout

If TXD is driven low for longer than approximately 25 ms, the LBUS pin is switched to Recessive mode and the part enters TOFF Mode. This is to prevent the LIN node from permanently driving the LIN Bus dominant. The transmitter is reenabled on TXD rising edge.

1.5.5 GROUND (VSS)

This is the Ground pin.

1.5.6 LIN BUS (LBUS)

The bidirectional LIN Bus pin (LBUS) is controlled by the TXD input. LBUS has a current limited open collector output. To reduce EMI, the edges during the signal changes are slope controlled and include corner rounding control for both falling and rising edges.

The internal LIN receiver observes the activities on the LIN bus, and matches the output signal RXD to follow the state of the LBUS pin.

1.5.6.1 Bus Dominant Timer

The Bus Dominant Timer is an internal timer that deactivates the LBUS transmitter after approximately 25 ms of dominant state on the LBUS pin. The timer is reset on any recessive LBUS state.

The LIN bus transmitter will be reenabled after a recessive state on the LBUS pin as long as CS is high. Disabling can be caused by the LIN bus being externally held dominant, or by TXD being driven low.

1.5.7 BATTERY (VBB)

This is the Battery Positive Supply Voltage pin.

1.5.8 VOLTAGE REGULATOR ENABLE OUTPUT (VREN)

This is the External Voltage Regulator Enable pin. Open-drain output is pulled high to VBB in all modes except Power-Down.

1.5.9 EXPOSED THERMAL PAD (EP)

Do not electrically connect, or connect to VSS.

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2.0 ELECTRICAL CHARACTERISTICS

2.1 Absolute Maximum Ratings†

V_{IN} DC Voltage on R_{XD}, T_{XD}, CS ..... -0.3 to +50V

V_{IN} DC Voltage on $\overline{WAKE}$ and V_{REN} ..... -0.3 to +V_{BB}

V_{BB} Battery Voltage, continuous, non-operating(1) ..... -0.3 to +50V

V_{BB} Battery Voltage, non-operating (LIN bus recessive)(2) ..... -0.3 to +60V

V_{BB} Battery Voltage, transient ISO 7637 Test 1 ..... -200V

V_{BB} Battery Voltage, transient ISO 7637 Test 2a ..... +150V

V_{BB} Battery Voltage, transient ISO 7637 Test 3a ..... -300V

V_{BB} Battery Voltage, transient ISO 7637 Test 3b ..... +200V

V_{LBUS} Bus Voltage, continuous ..... -18 to +50V

V_{LBUS} Bus Voltage, transient(3) ..... -27 to +60V

V_{LBUS} Bus Voltage, Direct Capacitor Coupling without TVS (SAE J2962-1) ..... ±35V and ±85V

I_{LBUS} Bus Short-Circuit Current Limit ..... 200 mA

ESD protection on LIN, without TVS (SAE J2962-1) ..... ±25 kV

ESD protection on LIN, V_{BB}, $\overline{WAKE}$ (IEC 61000-4-2)(4) ..... ±6 kV

ESD protection on LIN, V_{BB}, $\overline{WAKE}$, CS (Human Body Model)(5) ..... ±8 kV

ESD protection on all other pins (Human Body Model)(5) ..... ±4 kV

ESD protection on all pins (Charge Device Model)(6) ..... ±2 kV

ESD protection on all pins (Machine Model)(7) ..... ±400V

Maximum Junction Temperature ..... +150°C

Storage Temperature ..... -65 to +150°C

† NOTICE: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device, at those or any other conditions above those indicated in the operational listings of this specification, is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: LIN 2.x compliant specification.

2: SAE J2602 compliant specification.

3: ISO 7637/1 load dump compliant (t < 500 ms).

4: According to IEC 61000-4-2, 330Ω, 150 pF and Transceiver EMC Test Specifications [2] to [4]. For $\overline{WAKE}$ pin to meet the specification, series resistor must be in place (refer to Example 1-2).

5: According to AEC-Q100-002/JESD22-A114.

6: According to AEC-Q100-011B.

7: According to AEC-Q100-003/JESD22-A115.

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2.2 Nomenclature Used in This Document

Some terms and names used in this data sheet deviate from those referred to in the LIN specifications. Equivalent values are shown in Table 2-1.

TABLE 2-1: EQUIVALENT VALUES

LIN specifications Name	Term used in the following tables	Definition
V_{BAT}	*not used*	ECU operating voltage
V_{SUP}	V_{BB}	Supply voltage at device pin
I_{BUS_LIM}	I_{SC}	Current Limit of driver
V_{BUSREC}	$V_{IH(LBUS)}$	Recessive state
V_{BUSDOM}	$V_{IL(LBUS)}$	Dominant state

2.3 DC Specifications

DC Specifications	**Electrical Characteristics:** Unless otherwise indicated, all limits are specified for V_{BB} = 5.5V to 30.0V Extended (E): T_A = -40°C to +125°C High (H): T_A = -40°C to +150°C					
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Units**	**Conditions**
Power						
V_{BB} Quiescent Operating Current	I_{BBQ}	—	65	150	µA	Operating Mode, bus recessive
		—	—	160	µA	V_{BB} > 18V
V_{BB} Transmitter-off Current	I_{BBTO}	—	60	120	µA	Transmitter off, bus recessive
		—	—	130	µA	V_{BB} > 18V
V_{BB} Power-Down Current	I_{BBPD}	—	6	15	µA	
		—	—	20	µA	V_{BB} > 18V
		—	14	20	µA	LIN bus shorted to GND V_{LIN} = 0V, V_{BB} < 12V
V_{BB} Current with V_{SS} Floating	$I_{BBNOGND}$	-1	—	1	mA	V_{BB} = 12V, GND to V_{BB}, V_{LIN} = 0-27V
V_{BB} Undervoltage Threshold (switching from Operation mode to TOFF and V_{REN} OFF)	V_{BBUV_FALL}	3.8	4	4.4	V	V_{BB} falling **(Note 3)**
V_{BB} Undervoltage Recovery Threshold (switching from POR to Ready mode)	V_{BBUV_RISE}	5.5	5.6	6.0	V	V_{BB} rising **(Note 3)**
Microcontroller Interface						
High-Level Input Voltage (T_{XD})	V_{IH}	2.0	—	30	V	
Low-Level Input Voltage (T_{XD})	V_{IL}	-0.3	—	0.8	V	
High-Level Input Current (T_{XD})	I_{IH}	-5	—	—	µA	Input voltage = 4.0V

Note 1: Internal current limited. 2.0 ms maximum recovery time (R_{LBUS} = 0Ω, T_X = 0.4 V_{REG}, V_{LBUS} = V_{BB}).

2: Node has to sustain the current that can flow under this condition; bus must be operational under this condition.

3: Characterized; not 100% tested.

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2.3 DC Specifications (Continued)

DC Specifications	**Electrical Characteristics:** Unless otherwise indicated, all limits are specified for V_{BB} = 5.5V to 30.0V Extended (E): T_A = -40°C to +125°C High (H): T_A = -40°C to +150°C					
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Units**	**Conditions**
Low-Level Input Current (T_{XD})	I_{IL}	-12	—	—	µA	Input voltage = 0.5V
High-Level Voltage (V_{REN})	V_{HVREN}	-0.3	—	V_{BB} + 0.3	V	
High-Level Output Current (V_{REN})	I_{HVREN}	-40	—	-5	mA	Output voltage = V_{BB} - 0.5V
		-120	—	-20		Output voltage = V_{BB} - 2.0V
High-Level Input Voltage (CS)	V_{IH}	2.0	—	30	V	Through a current limiting resistor
Low-Level Input Voltage (CS)	V_{IL}	-0.3	—	0.8	V	
High-Level Input Current (CS)	I_{IH}	—	—	10.0	µA	Input voltage = 4.0V
Low-Level Input Current (CS)	I_{IL}	—	—	7.0	µA	Input voltage = 0.5V
Low-Level Input Voltage ($\overline{WAKE}$)	V_{IL}	V_{BB} - 4.0V	—	—	V	
High-Level Input Current ($\overline{WAKE}$)	I_{IH}	-12	—	—	µA	
		-15	—	—	µA	V_{BB} > 18V
Low-Level Input Current ($\overline{WAKE}$)	I_{IL}	-30	—	—	µA	
		-45	—	—	µA	V_{BB} > 18V
Low-Level Output Voltage (R_{XD})	V_{OL}	—	—	0.4	V	I_{IN} = 2 mA
Input Threshold Level (R_{XD})	$V_{TH(RXD)}$	—	2.5	—	V	R_{XD} > V_{TH}; LBUS recessive in Operating mode
High-Level Output Current (R_{XD})	I_{OH}	-1	—	-1	µA	V_{LIN} = V_{BB}, V_{RXD} = 5.5V
Bus Interface						
High-Level Input Voltage	$V_{IH(LBUS)}$	0.6 V_{BB}	—	—	V	Recessive state
Low-Level Input Voltage	$V_{IL(LBUS)}$	-8	—	0.4 V_{BB}	V	Dominant state
Input Hysteresis	V_{HYS}	—	—	0.175 V_{BB}	V	$V_{IH(LBUS)}$ - $V_{IL(LBUS)}$
Low-Level Output Current	$I_{OL(LBUS)}$	40	—	200	mA	Output voltage = 0.2 V_{BB}, V_{BB} = 12V
		16.5	—	—	mA	Output voltage = 0.2 V_{BB}, V_{BB} = 18V
High-Level Output Current	$I_{OH(LBUS)}$	—	—	20	µA	
Short-Circuit Current Limit	I_{SC}	50	—	200	mA	**(Note 1)**
High-Level Output Voltage	$V_{OH(LBUS)}$	0.8 V_{BB}	—	V_{BB}	V	
Driver Dominant Voltage	$V_{_LOSUP}$	—	—	1.2	V	R_{LOAD} = 500Ω
Input Leakage Current (at the receiver during dominant bus level)	$I_{BUS_PAS_DOM}$	-1	-0.4	—	mA	Driver off, V_{BUS} = 0V, V_{BB} = 12V

Note 1: Internal current limited. 2.0 ms maximum recovery time (R_{LBUS} = 0Ω, T_X = 0.4 V_{REG}, V_{LBUS} = V_{BB}).

2: Node has to sustain the current that can flow under this condition; bus must be operational under this condition.

3: Characterized; not 100% tested.

2.3 DC Specifications (Continued)

DC Specifications	**Electrical Characteristics:** Unless otherwise indicated, all limits are specified for V_{BB} = 5.5V to 30.0V Extended (E): T_A = -40°C to +125°C High (H): T_A = -40°C to +150°C					
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Units**	**Conditions**
Input Leakage Current (at the receiver during recessive bus level)	$I_{BUS_PAS_REC}$	—	12	20	µA	Driver off, 8V < V_{BB} < 18V 8V < V_{BUS} < 18V $V_{BUS} \geq V_{BB}$
Leakage Current (disconnected from ground)	$I_{BUS_NO_GND}$	-10	1.0	+10	µA	GND_{DEVICE} = V_{BB}, 0V < V_{BUS} < 18V, V_{BB} = 12V
Leakage Current (disconnected from V_{BB})	$I_{BUS_NO_VBB}$	—	—	10	µA	V_{BB} = GND, 0 < V_{BUS} < 18V, **(Note 2)**
Receiver Center Voltage	V_{BUS_CNT}	0.475 V_{BB}	0.5 V_{BB}	0.525 V_{BB}	V	V_{BUS_CNT} = (V_{IL} (L_{BUS}) + V_{IH} (L_{BUS}))/2
Slave Termination	R_{SLAVE}	20	30	60	kΩ	
Capacitance of Slave Node	C_{SLAVE}	—	—	100	pF	**(Note 3)**

Note 1: Internal current limited. 2.0 ms maximum recovery time (R_{LBUS} = 0Ω, T_X = 0.4 V_{REG}, V_{LBUS} = V_{BB}).

2: Node has to sustain the current that can flow under this condition; bus must be operational under this condition.

3: Characterized; not 100% tested.

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2.4 AC Specifications

AC Characteristics	**Electrical Characteristics:** Unless otherwise indicated, all limits are specified for V_{BB} = 5.5V to 27.0V Extended (E): T_A = -40°C to +125°C High (H): T_A = -40°C to +150°C					
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Units**	**Test Conditions**
Bus Interface – Constant Slope Time Parameters						
Slope Rising and Falling Edges	t_{SLOPE}	3.5	—	22.5	µs	7.3V ≤ V_{BB} ≤ 18V
Propagation Delay of Transmitter	$t_{TRANSPD}$	—	—	4.0	µs	$t_{TRANSPD}$ = max ($t_{TRANSPDR}$ or $t_{TRANSPDF}$)
Propagation Delay of Receiver	t_{RECPD}	—	—	6.0	µs	t_{RECPD} = max (t_{RECPDR} or t_{RECPDF})
Symmetry of Propagation Delay of Receiver Rising Edge w.r.t. Falling Edge	t_{RECSYM}	-2.0	—	2.0	µs	t_{RECSYM} = max (t_{RECPDF} - t_{RECPDR}) R_{RXD} 2.4Ω to V_{CC}, C_{RXD} 20 pF
Symmetry of Propagation Delay of Transmitter Rising Edge w.r.t. Falling Edge	$t_{TRANSSYM}$	-2.0	—	2.0	µs	$t_{TRANSSYM}$ = max ($t_{TRANSPDF}$ - $t_{TRANSPDR}$)
Duty Cycle 1 @20.0 kbit/sec		0.396	—	—	—	C_{BUS}; R_{BUS} conditions: 1 nF; 1 kΩ | 6.8 nF; 660Ω | 10 nF; 500Ω $TH_{REC(MAX)}$ = 0.744 × V_{BB}, $TH_{DOM(MAX)}$ = 0.581 × V_{BB}, V_{BB} =7.0V - 18V; t_{BIT} = 50 µs D1 = $t_{BUS_REC(MIN)}$/2 × t_{BIT})
Duty Cycle 2 @20.0 kbit/sec		—	—	0.581	—	C_{BUS}; R_{BUS} conditions: 1 nF; 1 kΩ | 6.8 nF; 660Ω | 10 nF; 500Ω $TH_{REC(MAX)}$ = 0.284 × V_{BB}, $TH_{DOM(MAX)}$ = 0.422 × V_{BB}, V_{BB} =7.6V - 18V; t_{BIT} = 50 µs D2 = $t_{BUS_REC(MAX)}$/2 × t_{BIT})
Duty Cycle 3 @10.4 kbit/sec		0.417	—	—	—	C_{BUS}; R_{BUS} conditions: 1 nF; 1 kΩ | 6.8 nF; 660Ω | 10 nF; 500Ω $TH_{REC(MAX)}$ = 0.778 × V_{BB}, $TH_{DOM(MAX)}$ = 0.616 × V_{BB}, V_{BB} =7.0V – 18V; t_{BIT} = 96 µs D3 = $t_{BUS_REC(MIN)}$/2 × t_{BIT})
Duty Cycle 4 @10.4 kbit/sec		—	—	0.590	—	C_{BUS}; R_{BUS} conditions: 1 nF; 1 kΩ | 6.8 nF; 660Ω | 10 nF; 500Ω TH_{REC}(max) = 0.251 × V_{BB}, $TH_{DOM(MAX)}$ = 0.389 × V_{BB}, V_{BB} =7.6V – 18V; t_{BIT} = 96 µs D4 = $t_{BUS_REC(MAX)}$/2 × t_{BIT})
Wake-up Timing						
Bus Activity Debounce time	t_{BDB}	30	70	125	µs	
Bus Activity to V_{REN} on	t_{BACTVE}	10	60	110	µs	
$\overline{WAKE}$ to V_{REN} on	t_{WAKE}	—	—	150	µs	
Chip Select to V_{REN} on	t_{CSOR}	—	—	150	µs	V_{REN} floating
Chip Select to V_{REN} off	t_{CSPD}	—	—	200	µs	V_{REN} floating

2.5 Thermal Specifications

Parameter	Symbol	Typ.	Max.	Units	Test Conditions
Recovery Temperature	$\theta_{RECOVERY}$	+160	—	°C	
Shutdown Temperature	$\theta_{SHUTDOWN}$	+180	—	°C	
Short-Circuit Recovery Time	t_{THERM}	1.5	5.0	ms	
Thermal Package Resistances					
Thermal Resistance, 2x3 8L-DFN	θ_{JA}	75	—	°C/W	
Thermal Resistance, 3x3 8L-DFN	θ_{JA}	56.7	—	°C/W	
Thermal Resistance, 8L-SOIC	θ_{JA}	149.5	—	°C/W	

Note 1: The maximum power dissipation is a function of T_{JMAX}, θ_{JA} and ambient temperature T_A. The maximum allowable power dissipation at an ambient temperature is $P_D = (T_{JMAX} - T_A)\ \theta_{JA}$. If this dissipation is exceeded, the die temperature will rise above 150°C and the device will go into thermal shutdown.

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2.6 Typical Performance Curves

Note:	The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, V_{BB} = 5.5V to 18.0V, Extended (E): T_A = -40°C to +125°C and High (H): T_A = -40°C to +150°C.

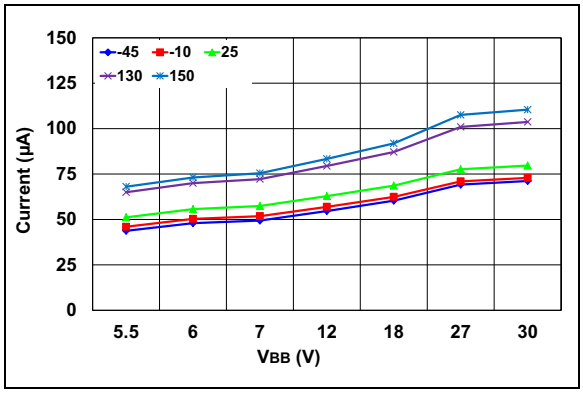


FIGURE 2-1: *Typical I_{BBQ}.*

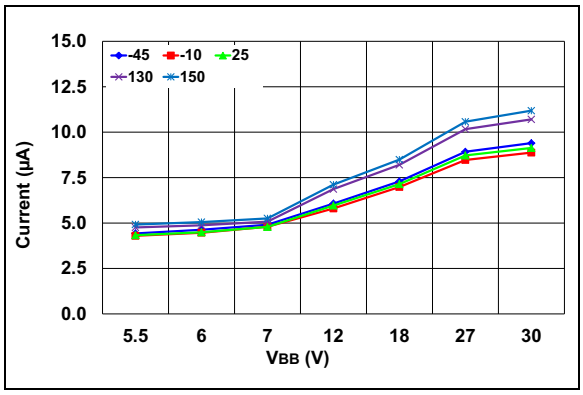


FIGURE 2-2: *Typical I_{BBPD}.*

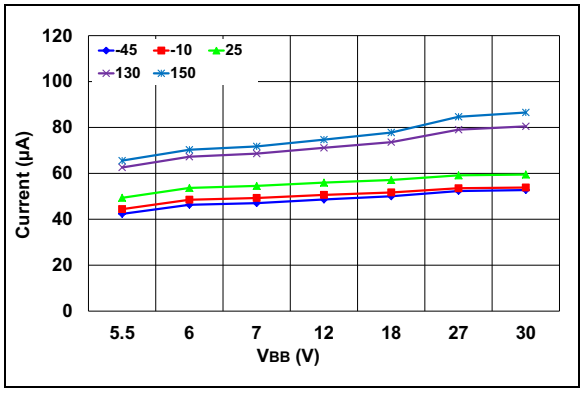


FIGURE 2-3: *Typical I_{BBTO}.*

2.7 Timing Diagrams and Specifications

FIGURE 2-4: BUS TIMING DIAGRAM

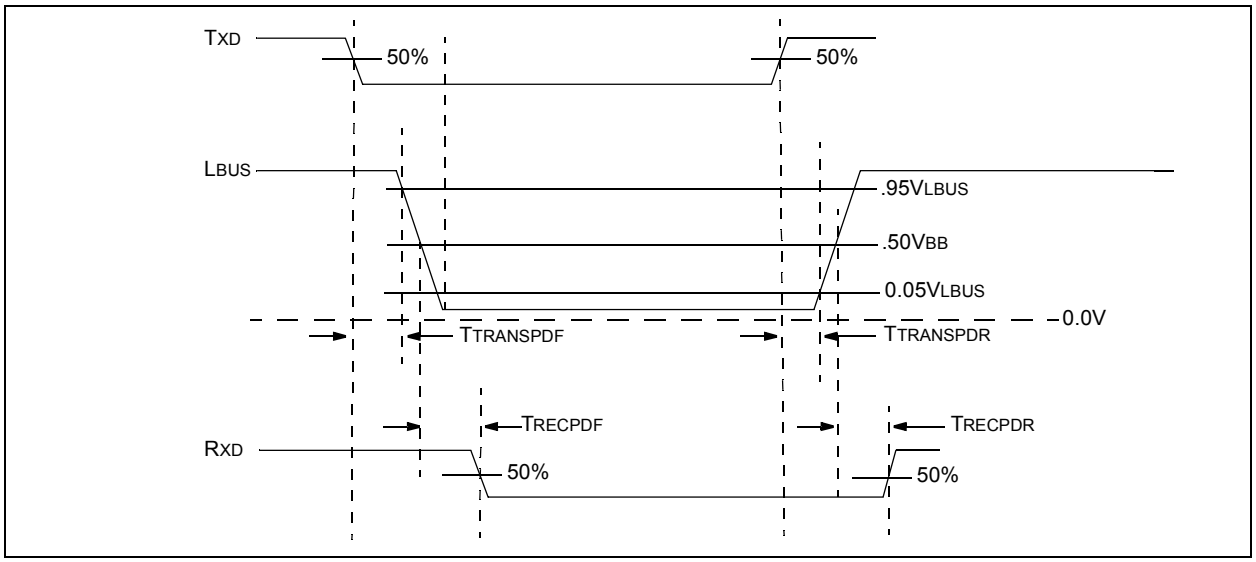


FIGURE 2-5: CS TO VREN TIMING DIAGRAM

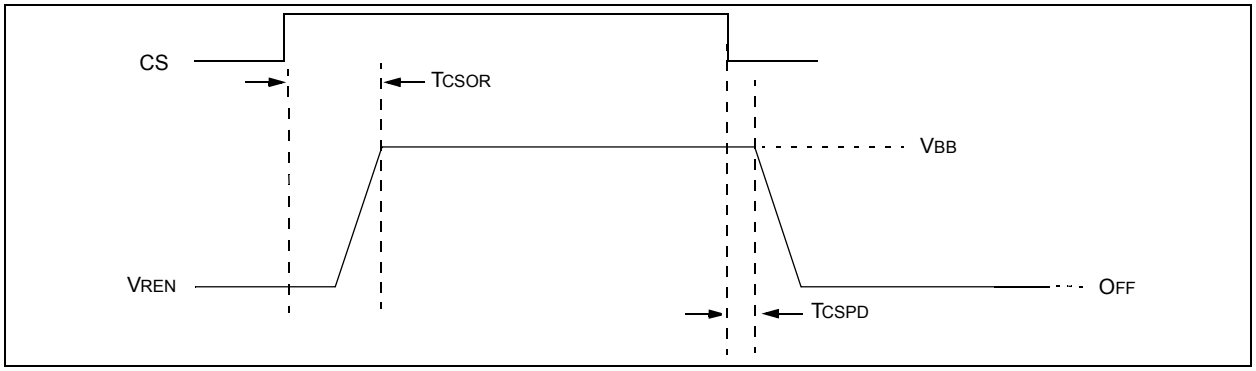
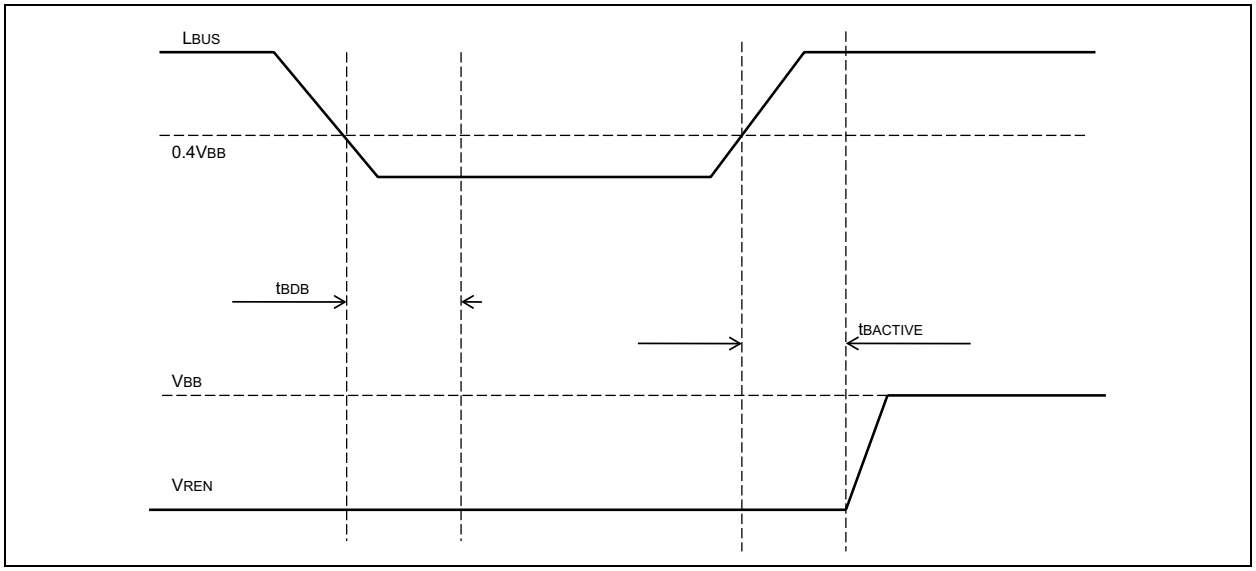


FIGURE 2-6: REMOTE WAKE-UP



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3.0 PACKAGING INFORMATION

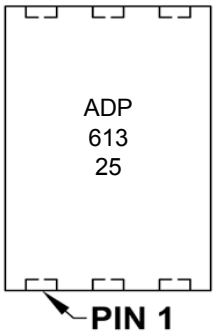
3.1 Package Marking Information

8-Lead DFN (2x3)

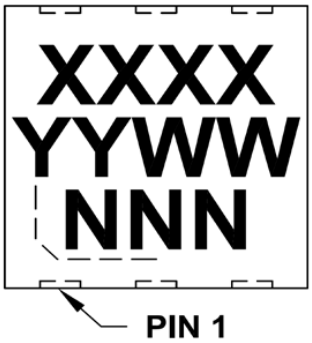


Device	Code
MCP2003B-E/MC	ADP
MCP2003BT-E/MC	ADP
MCP2003B-H/MC	ADR
MCP2003BT-H/MC	ADR

Examples:

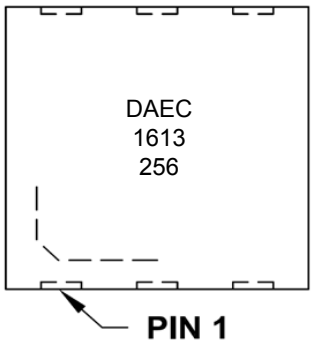


8-Lead DFN (3x3)

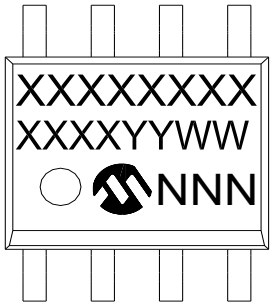


Device	Code
MCP2003B-E/MF	DAEC
MCP2003BT-E/MF	DAEC
MCP2003B-H/MF	DAEE
MCP2003BT-H/MF	DAEE

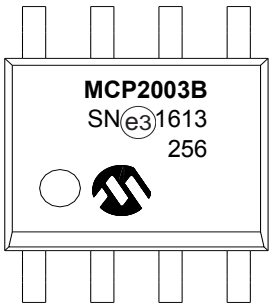
Examples:



8-Lead SOIC (150 mil)



Examples:

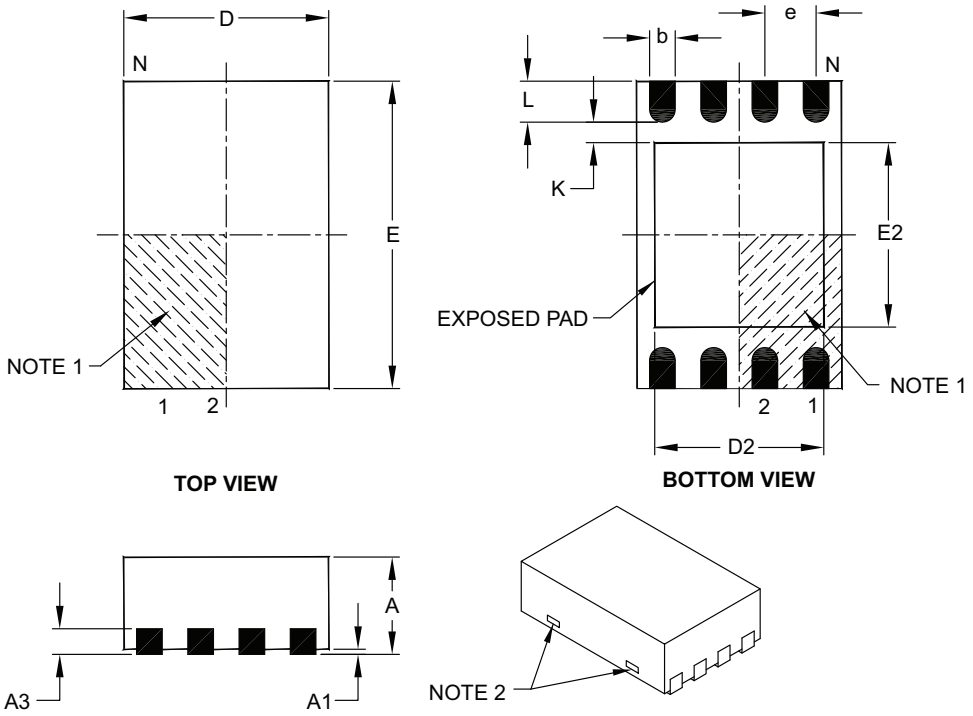


Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

8-Lead Plastic Dual Flat, No Lead Package (MC) – 2x3x0.9 mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		0.50 BSC	
Overall Height	A	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3		0.20 REF	
Overall Length	D		2.00 BSC	
Overall Width	E		3.00 BSC	
Exposed Pad Length	D2	1.30	–	1.55
Exposed Pad Width	E2	1.50	–	1.75
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.30	0.40	0.50
Contact-to-Exposed Pad	K	0.20	–	–

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Package may have one or more exposed tie bars at ends.
3. Package is saw singulated.
4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

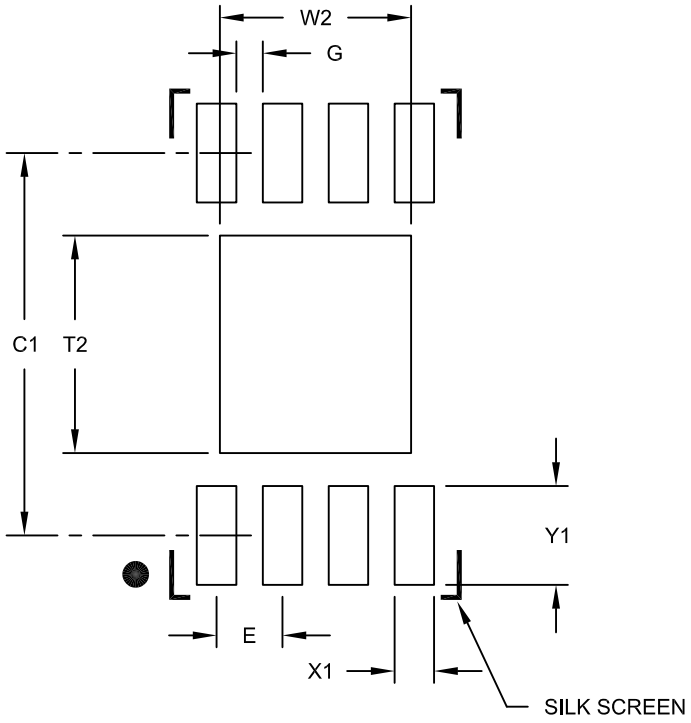
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-123C

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8-Lead Plastic Dual Flat, No Lead Package (MC) - 2x3x0.9mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	0.50 BSC		
Optional Center Pad Width	W2			1.45
Optional Center Pad Length	T2			1.75
Contact Pad Spacing	C1		2.90	
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.20		

Notes:

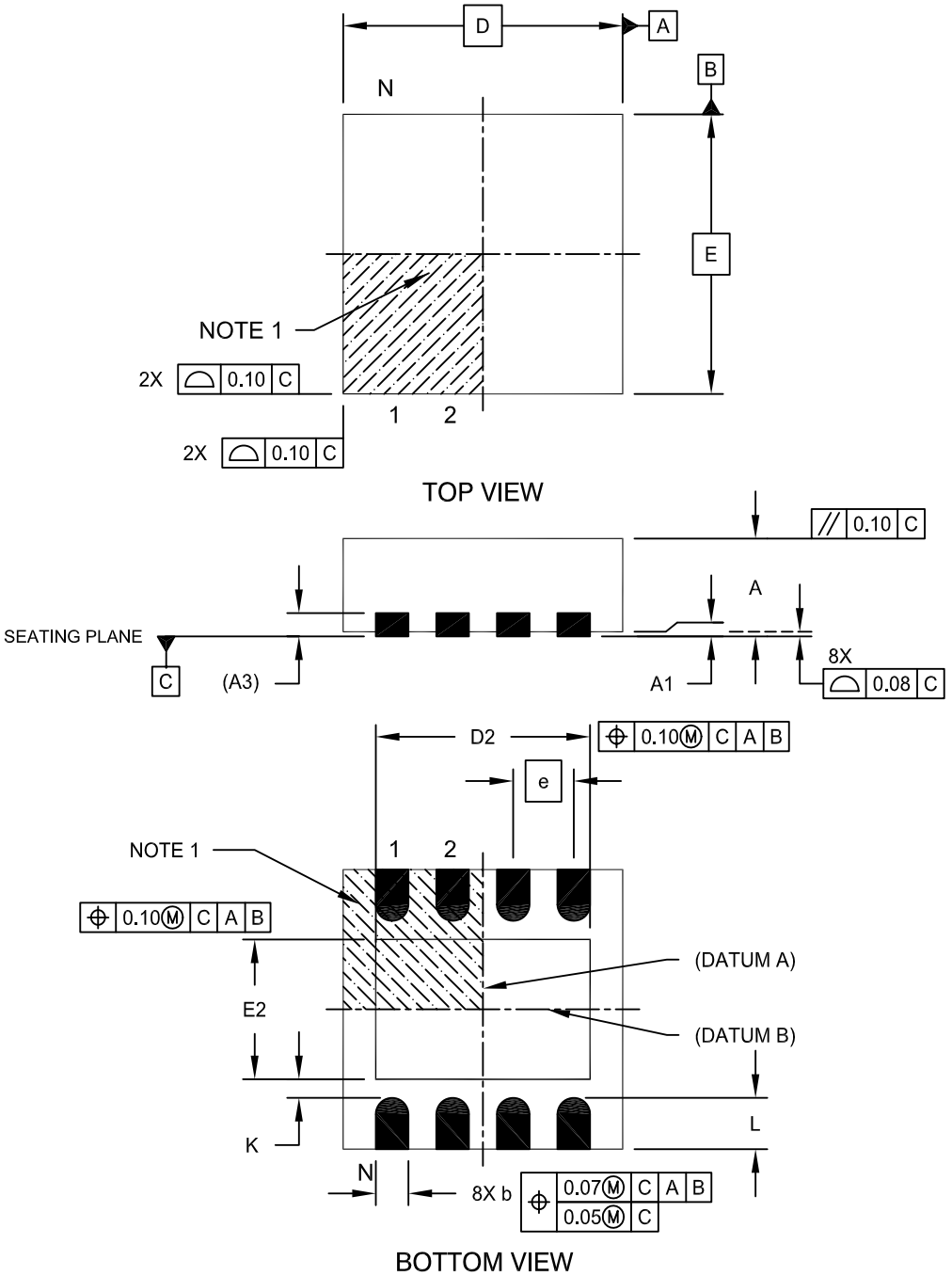
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2123B

8-Lead Plastic Dual Flat, No Lead Package (MF) - 3x3x0.9mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

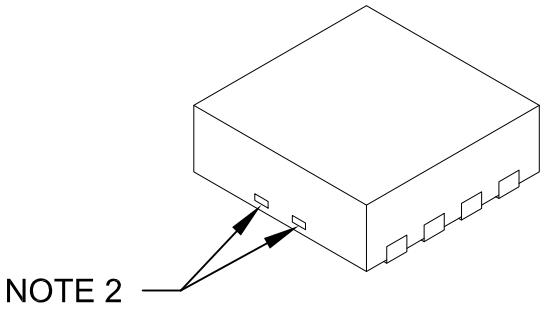


Microchip Technology Drawing No. C04-062C Sheet 1 of 2

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8-Lead Plastic Dual Flat, No Lead Package (MF) - 3x3x0.9mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		0.65 BSC	
Overall Height	A	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3		0.20 REF	
Overall Length	D		3.00 BSC	
Exposed Pad Width	E2	1.34	-	1.60
Overall Width	E		3.00 BSC	
Exposed Pad Length	D2	1.60	-	2.40
Contact Width	b	0.25	0.30	0.35
Contact Length	L	0.20	0.30	0.55
Contact-to-Exposed Pad	K	0.20	-	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Package may have one or more exposed tie bars at ends.
3. Package is saw singulated
4. Dimensioning and tolerancing per ASME Y14.5M

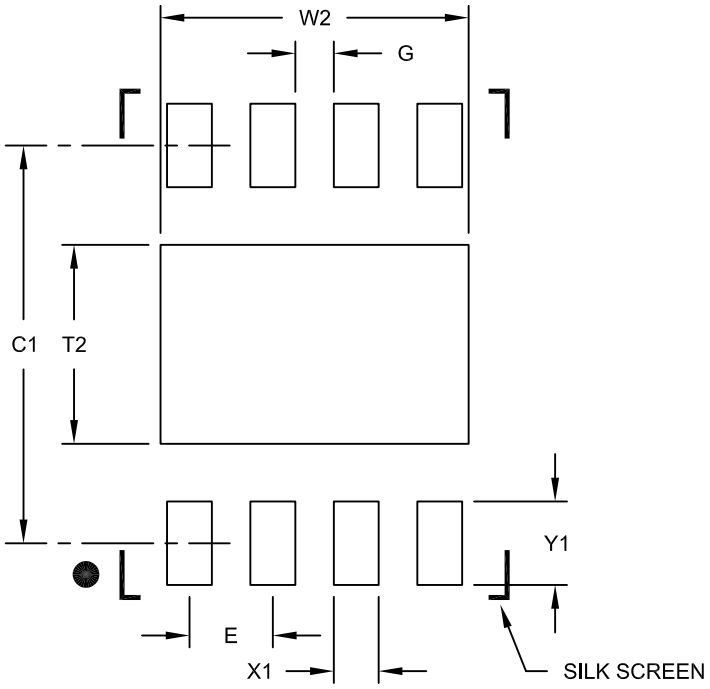
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-062C Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MF) - 3x3x0.9mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Optional Center Pad Width	W2			2.40
Optional Center Pad Length	T2			1.55
Contact Pad Spacing	C1		3.10	
Contact Pad Width (X8)	X1			0.35
Contact Pad Length (X8)	Y1			0.65
Distance Between Pads	G	0.30		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

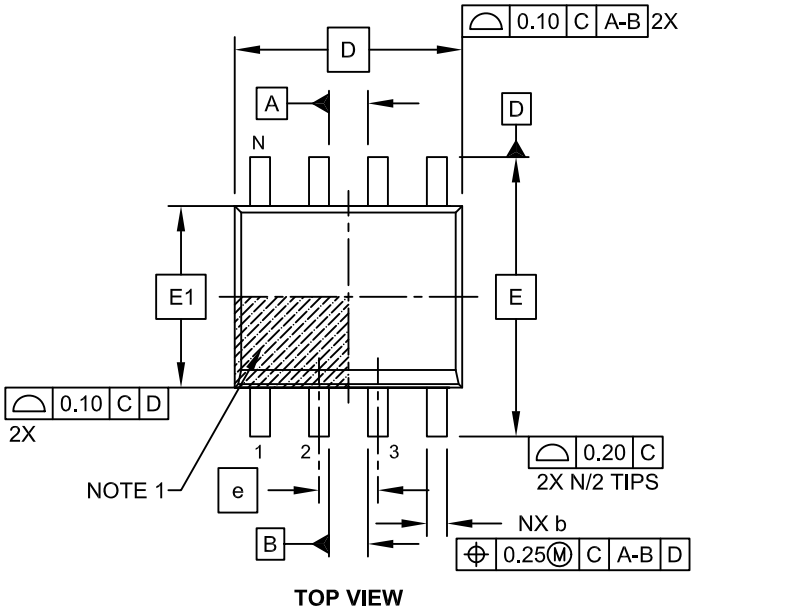
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2062B

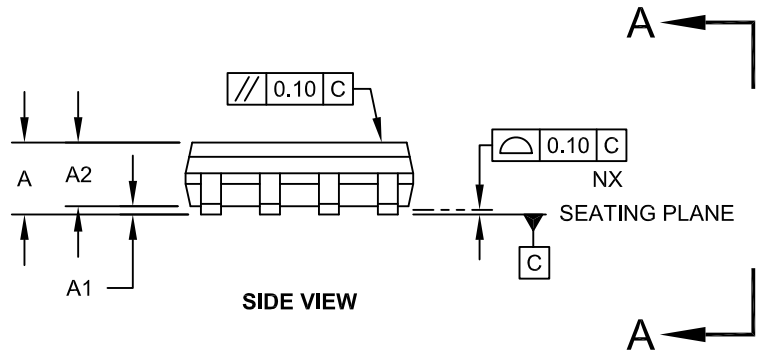
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8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

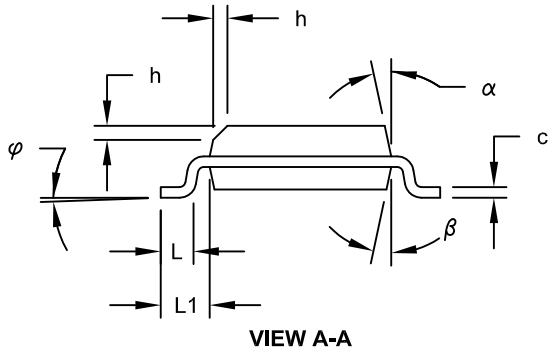
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



TOP VIEW



SIDE VIEW

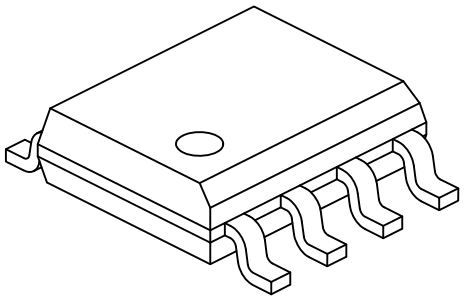


VIEW A-A

Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		1.27 BSC	
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E		6.00 BSC	
Molded Package Width	E1		3.90 BSC	
Overall Length	D		4.90 BSC	
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.17	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

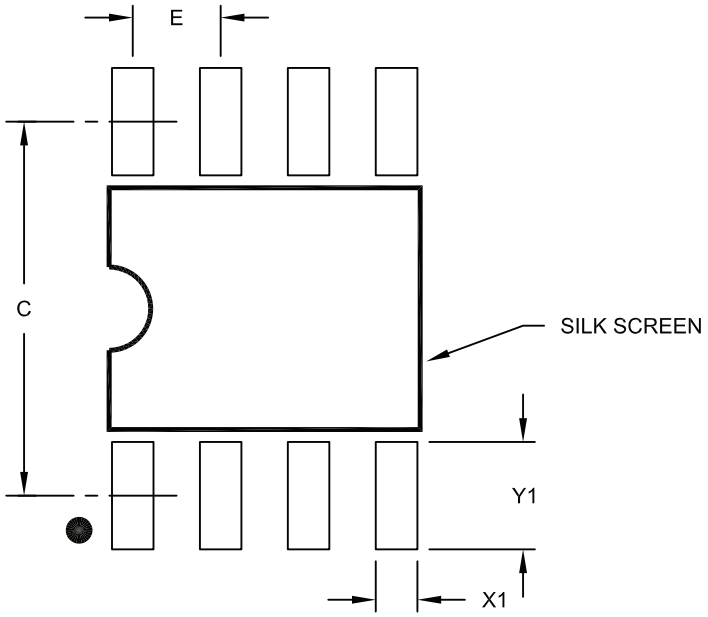
   REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

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8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

NOTES:

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APPENDIX A: REVISION HISTORY

Revision C (April 2016)

The following is the list of modifications:

- Updated **MCP2003B Block Diagram**.
- Updated **Section 1.3.1, Power-Down Mode**.
- Updated **Figure 1-2**.
- Updated **Table 1-1**.
- Added V_{BBUV_FALL}, V_{BBUV_RISE} and updated I_{BBPD}.

Revision B (December 2015)

The following is the list of modifications:

- Included Features and Electrical Characteristics for the SAE J2962-1.
- Minor typographical changes.

Revision A (November 2015)

- Original release of this document.

NOTES:

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PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	X	/XX
Device	Temperature Range	Package

Device:	MCP2003B: LIN Transceiver MCP2003BT: LIN Transceiver (Tape and Reel)
Temperature Range:	E = -40°C to +125°C (Extended) H = -40°C to +150°C (High)
Package:	MC = 8-Lead Plastic Dual Flat, No Lead Package – 2x3x0.9 mm Body (DFN) MF = 8-Lead Plastic Dual Flat, No Lead Package – 3x3x0.9 mm Body (DFN) SN = 8-Lead Plastic Small Outline – Narrow 3.90 mm Body (SOIC)

Examples:

a) MCP2003B-E/MC: Extended Temperature, 8LD 2x3 DFN package

b) MCP2003B-E/MF: Extended Temperature, 8LD 3x3 DFN package

c) MCP2003B-E/SN: Extended Temperature, 8LD SOIC package

d) MCP2003BT-H/MC: Tape and Reel, High Temperature, 8LD 2x3 DFN package

e) MCP2003BT-H/MF: Tape and Reel, High Temperature, 8LD 3x3 DFN package

f) MCP2003BT-H/SN: Tape and Reel, High Temperature, 8LD SOIC package

NOTES:

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Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
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